

參考文獻

- 1 Jewon Lee et al., "Dry etching of GaN and related materials comparison of techniques" Selected Topics in Quantum Electronics, IEEE Journal of Volume 4, Issue 3, May-June 1998 Page(s):557 – 563
- 2 X. A. Cao et al., "GaN N- and P-Type Schottky Diodes: Effect of Dry Etch Damage" IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 47, NO. 7, JULY 2000 page 1320 - 1324
- 3 O. Ambacher et al., "Two-dimensional electron gases induced by spontaneous and piezoelectric polarization charges in N- and Ga-face AlGaIn/GaN heterostructures," Journal of Applied Physics, Vol 85, Num 6,(3222), 1999.
- 4 R.Dimitrov et al., "Two-dimensional electron gases in Ga-face and N-face AlGaIn/GaN heterostructures grown by plasma-induced molecular beam epitaxy and Metalorganic chemical vapor deposition on sapphire", Journal of Applied Physics, Vol 87, Num 7, (3375), 2000.
- 5 Hadis Morkoc et al., "GaN-based modulation doped FETs and UV detectors," Solid-State Electronics 46, 157-202, 2002.
- 6 O.Ambacher et al., "Two dimensional electron gases induced by spontaneous and piezoelectric polarization in undoped AlGaIn/GaN heterostructures" Journal of Applied Physics, Vol 87, Num 1, (334), 2000.
- 7 I.P. Smorchkova et al., "Polarization-induced charge and electron mobility in AlGaIn/GaN heterostructures grown by plasma-assisted molecular-beam epitaxy," Journal of Applied Physics, Vol 86, Num 8, (4520), 1999.
- 8 Fabio Sacconi et al., "Spontaneous and Piezoelectric Polarization Effects on the Output Characteristics of AlGaIn/GaN Heterojunction Modulation Doped FETs," IEEE Trans. Electron Devices, VOL. 48, NO3, March 2001.

9. Lester F. Eastman et al., "Undoped AlGaIn/GaN HEMTs for Microwave Power Application," IEEE Trans. Electron Devices, VOL. 48, NO3, (479) 2001.
10. Ando, Y et al., "A 110-W AlGaIn-GaN heterojunction FET on thinned sapphire substrate" 2001 IEDM Page(s): 17.3.1-17.3.4
11. M.S. Shur and M.A. Kahn, "Wide Band Gap Semiconductors. Good Results and Great Expectations", in the Proceedings of 23d International Symposium on GaAs and Related Compounds, St. Petersburg, Russia, Sep. 22-28, 1996, Institute Phys. Conference Series, No.155, Chapter 2, pp. 25-32, M.S. Shur and R. Suris, Editors, IOP Publishing, London 1997.
12. Y. Ando et al., "12 W per mm recessed-gate AlGaIn-GaN heterojunction field-plate " FET2003 IEDM Page(s) 23.1.1- 23.1.4
13. Yasuhiro Okamoto *et al.*, "High-power recessed-gate AlGaIn-GaN HFET with a field-modulating plate" 2004 IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 51, NO. 12, Page(s) 2217-2222
14. L .Shen "Advanced Polarization-Based Design of AlGaIn/GaN HEMTs" University of California Santa Barbara ,2002
15. M.S. Shur and M.A. Kahn, "Wide Band Gap Semiconductors. Good Results and Great Expectations", in the Proceedings of 23d International Symposium on GaAs and Related Compounds, St. Petersburg, Russia, Sep. 22-28, 1996, Institute Phys. Conference Series, No.155, Chapter 2, pp. 25-32, M.S. Shur and R. Suris, Editors, IOP Publishing, London 1997.
16. IEEE spectrum, May 2002.